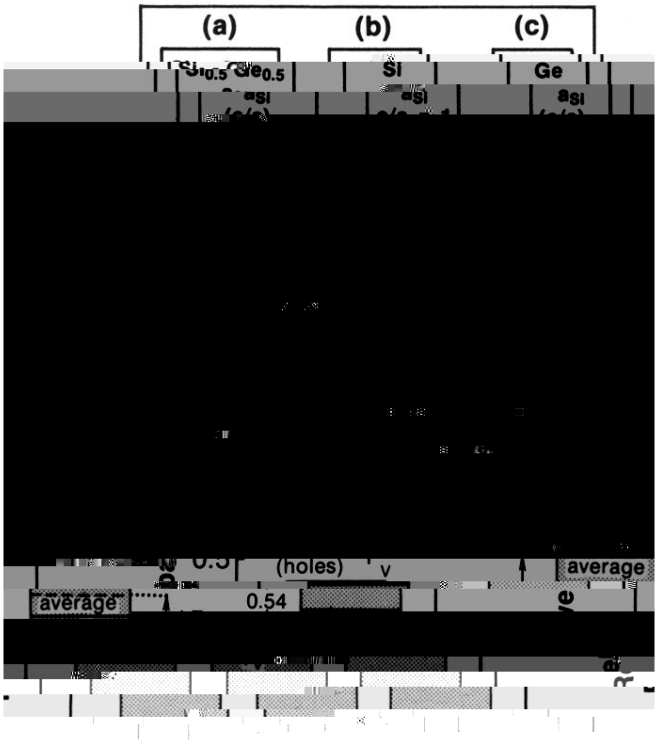

FIG. 2. Band-structure discontinuities of $Si_{0.5}Ge_{0.5}$/Si [(a)] and Ge/Si [(b) and (c)]. The valence-band offsets ΔE_v [illegible] are taken from Ref. 16. Relative conduction-band offsets are [illegible] by positioning the [illegible] energy of Γ_v [illegible] (denoted "average") of one material at a distance ΔE [illegible] from the average of the other [illegible]